Supporting Information

Effect of a graphene oxide intermediate layer in Cu₂ZnSn(S,Se)₄ solar cells

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Fig. S1 Cross-sectional FE-SEM images of a GO layer deposited using different deposition cycles: (a) 3, (b) 7 and (c) 11 times on a Mo/glass substrate



Fig. S2 EDS mapping results on a GO/Mo surface; numerous carbon and oxygen peaks are observed for the GO/Mo surface

Raman results (T1)



Fig. S3 Raman spectra for samples with and without a GO layer at T1



Fig. S4 Elemetal mapping result for CZTSSe solar cell with a GO layer. A growth of $MoSe_2$ layer is not observed at the interface.



Fig. S5 UV-Vis absorption spectra for CZTSSe film with and without a GO layer